



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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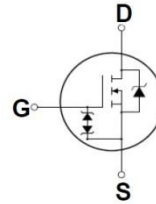
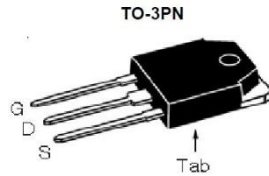


N-channel MOSFET

## Features

- Low gate charge
- 100% avalanche tested
- Improved dv/dt capability
- RoHS compliant
- JEDEC Qualification
- Improved ESD performance

$BV_{DSS}$	$I_D$	$R_{DS(on)}$
800V	12A	< 0.65Ω



Device	Package	Marking	Remark
GP2M012A080NG	TO-3PN	GP2M012A080NG	RoHS

## Absolute Maximum Ratings

Parameter	Symbol	value	Unit
Drain-Source Voltage	$V_{DS}$	800	V
Gate-Source Voltage	$V_{GS}$	±30	V
Continuous Drain Current	$I_D$	$T_C = 25\text{ °C}$	12
		$T_C = 100\text{ °C}$	10
Pulsed Drain Current (Note 1)	$I_{DM}$	48	A
Single Pulse Avalanche Energy (Note 2)	$E_{AS}$	313	mJ
Repetitive Avalanche Current (Note 1)	$I_{AR}$	12	A
Repetitive Avalanche Energy (Note 1)	$E_{AR}$	41.6	mJ
Power Dissipation	$P_D$	$T_C = 25\text{ °C}$	416
		Derate above 25 °C	3.3
Peak Diode Recovery dv/dt (Note 3)	dv/dt	4.5	V/ns
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~150	°C
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	$T_L$	300	°C

\* Limited only by maximum junction temperature

## Thermal Characteristics

Parameter	Symbol	value	Unit
Maximum Thermal resistance, Junction-to-Case	$R_{\theta JC}$	0.3	°C/W
Maximum Thermal resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W

**Electrical Characteristics :  $T_C=25^\circ\text{C}$ , unless otherwise noted**

Parameter	Symbol	Test condition	Min	Typ	Max	Units
<b>OFF</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	600	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	$\mu\text{A}$
		$V_{DS} = 640\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	$\mu\text{A}$
Forward Gate-Source Leakage Current	$I_{GSSF}$	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	$\mu\text{A}$
Reverse Gate-Source Leakage Current	$I_{GSSR}$	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	$\mu\text{A}$

**ON**

Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	3	--	5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 6.0\text{ A}$	--	0.53	0.65	$\Omega$
Forward Transconductance <sup>(Note 4)</sup>	$g_{FS}$	$V_{DS} = 30\text{ V}, I_D = 6.0\text{ A}$	--	18	--	S

**DYNAMIC**

Input Capacitance	$C_{iss}$	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	3370	--	pF
Output Capacitance	$C_{oss}$		--	310	--	pF
Reverse Transfer Capacitance	$C_{rss}$		--	33	--	pF

**SWITCHING**

Turn-On Delay Time <sup>(Note 4,5)</sup>	$t_{d(on)}$	$V_{DD} = 400\text{ V}, I_D = 12\text{ A},$ $R_G = 25\ \Omega$	--	81	--	ns
Turn-On Rise Time <sup>(Note 4,5)</sup>	$t_r$		--	90	--	ns
Turn-Off Delay Time <sup>(Note 4,5)</sup>	$t_{d(off)}$		--	266	--	ns
Turn-Off Fall Time <sup>(Note 4,5)</sup>	$t_f$		--	63	--	ns
Total Gate Charge <sup>(Note 4,5)</sup>	$Q_g$	$V_{DS} = 640\text{ V}, I_D = 12\text{ A},$ $V_{GS} = 10\text{ V}$	--	79	--	nC
Gate-Source Charge <sup>(Note 4,5)</sup>	$Q_{gs}$		--	16	--	nC
Gate-Drain Charge <sup>(Note 4,5)</sup>	$Q_{gd}$		--	37	--	nC

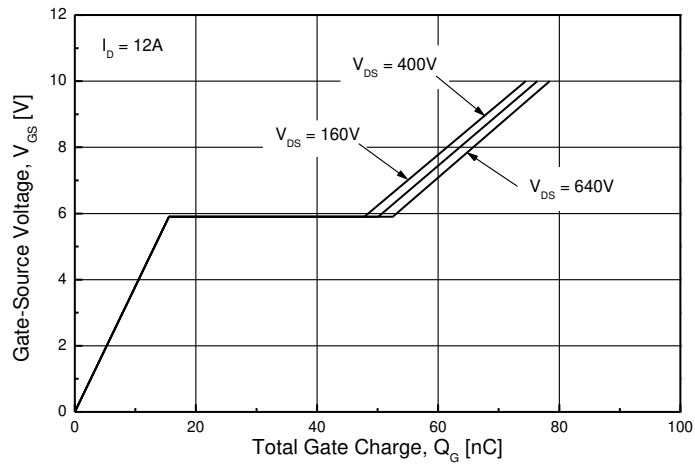
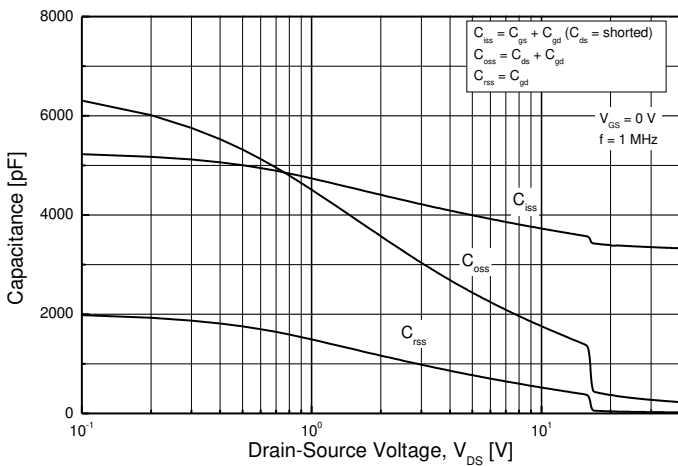
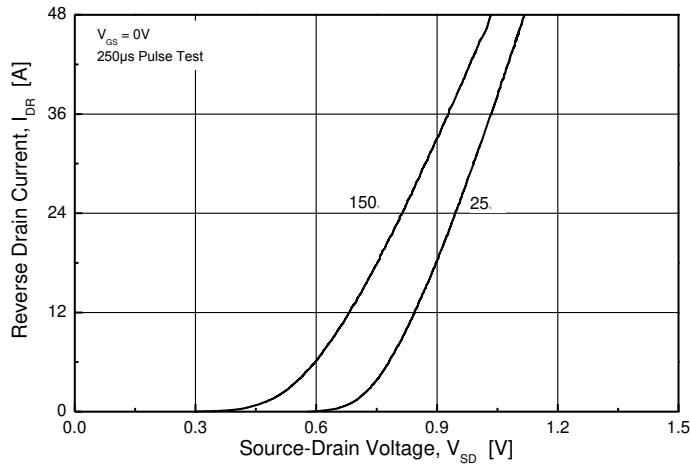
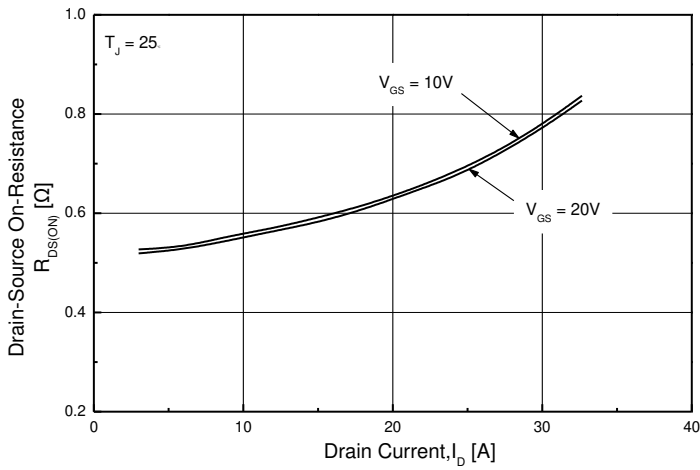
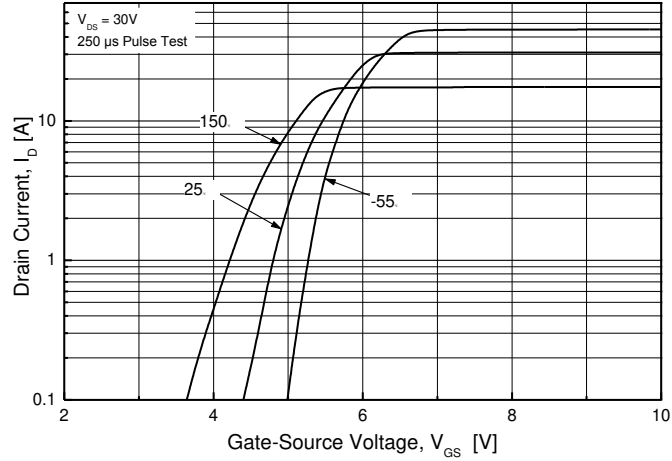
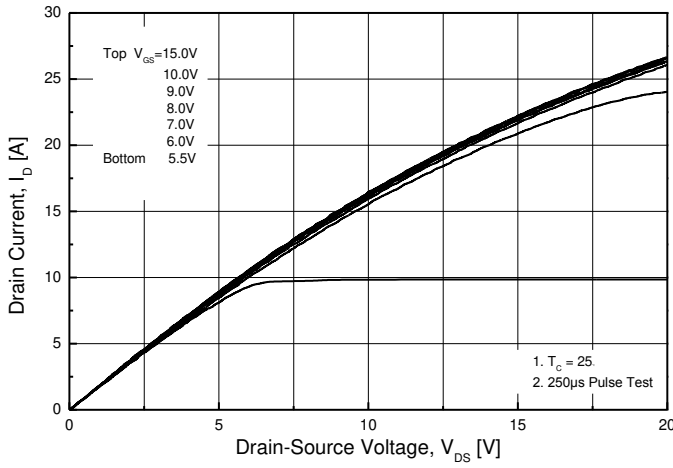
**SOURCE DRAIN DIODE**

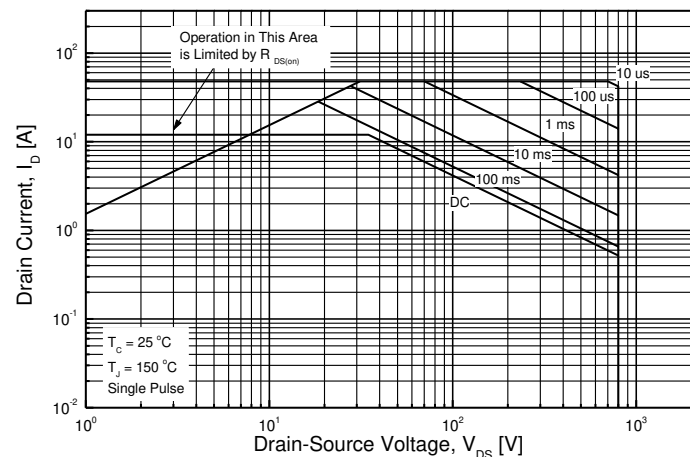
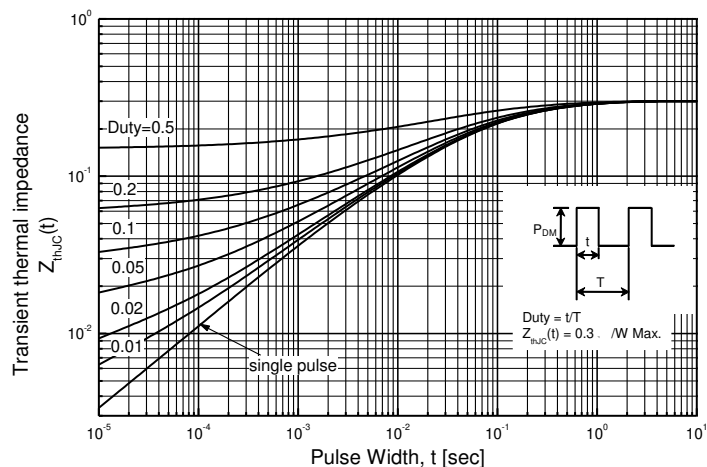
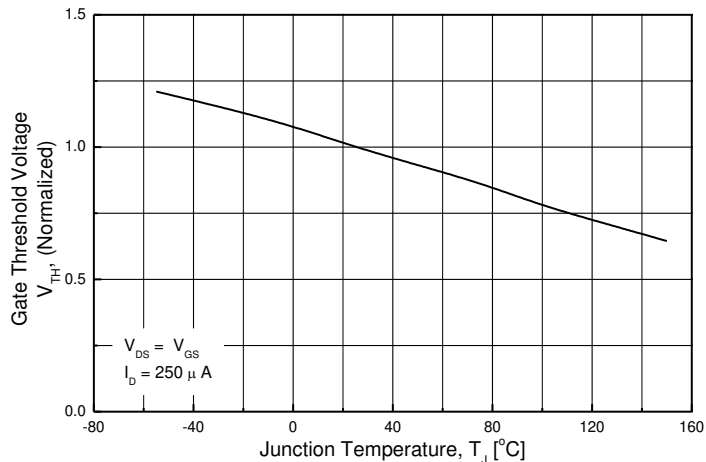
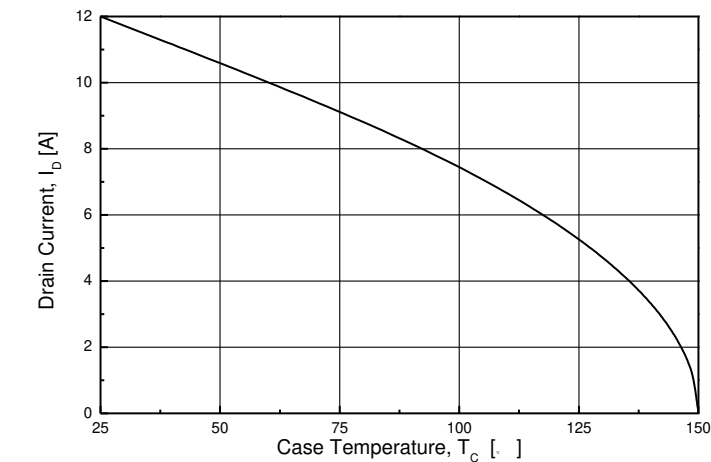
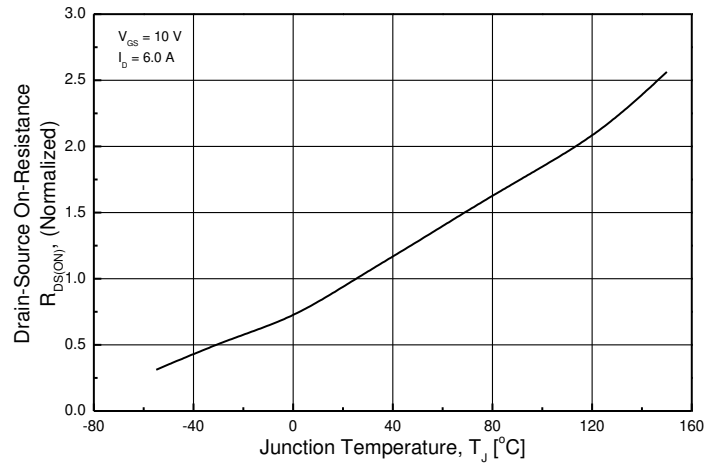
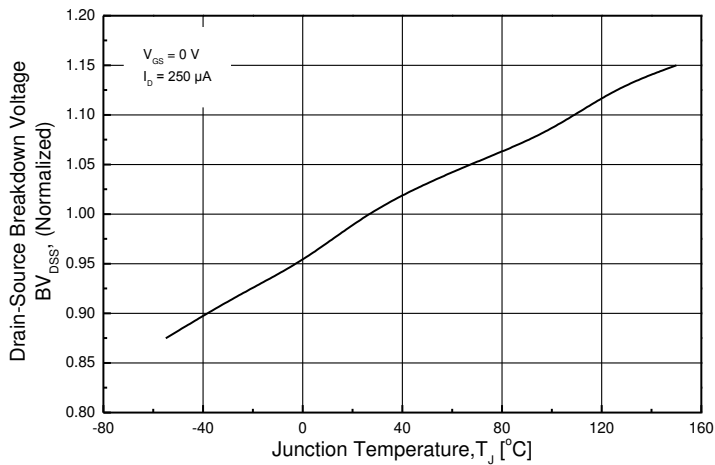
Maximum Continuous Drain-Source Diode Forward Current	$I_S$	---	--	--	12	A
Maximum Pulsed Drain-Source Diode Forward Current	$I_{SM}$	---	--	--	48	A
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0\text{ V}, I_S = 12\text{ A}$	--	--	1.5	V
Reverse Recovery Time <sup>(Note 4)</sup>	$t_{rr}$	$V_{GS} = 0\text{ V}, I_S = 12\text{ A}$ $di_F / dt = 100\text{ A}/\mu\text{s}$	--	528	--	ns
Reverse Recovery Charge <sup>(Note 4)</sup>	$Q_{rr}$		--	6.7	--	$\mu\text{C}$

Note :

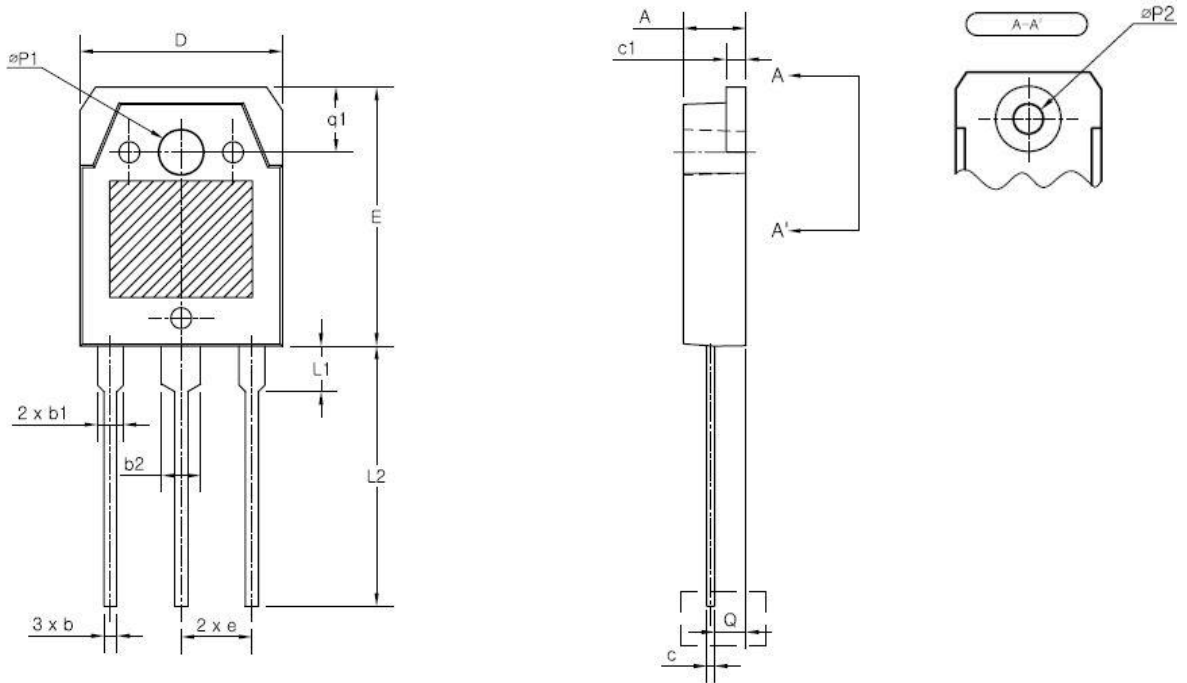
1. Repeated rating : Pulse width limited by safe operating area
2.  $L=4.08\text{mH}, I_{AS} = 12\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega,$  Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 12\text{A}, di/dt \leq 200\text{A}/\mu\text{s}, V_{DD} \leq BV_{DS},$  Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\mu\text{s},$  Duty Cycle  $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics







TO-3PN MECHANICAL DATA



SYMBOL	MIN	NOM	MAX
A	4.60	4.80	5.00
b	0.80	1.00	1.20
b1	1.80	2.00	2.20
b2	2.80	3.00	3.20
c	0.55	0.60	0.75
c1	1.45	1.50	1.65
D	15.40	15.60	15.80
E	19.70	19.90	20.10
e	5.15	5.45	5.75
L1	3.30	3.50	3.70
L2	19.80	20.00	20.20
$\varnothing P1$	3.30	3.40	3.50
$\varnothing P2$	(3.20)		
Q	2.20	2.40	2.60
q1	4.80	5.00	5.20

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